## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Kevin W. Glass

Title:

FREQUENCY PRESCALER APPARATUS, METHOD, AND SYSTEM

Docket No.:

80107.022US1

Filed:

June 27, 2003

Examiner:

Unknown

Commissioner for Patents

P.O.Box 1450

Alexandria, VA 22313-1450

Serial No.: 10/608051

Due Date: N/A

Group Art Unit: Unknown

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## INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents P.O.Box 1450 Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 et. seq., the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicant respectfully requests that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicant requests that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicant with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 50-2359 in order to have this Information Disclosure Statement considered.

The Examiner is invited to contact the Applicant's Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

KEVIN W. GLASS

By his Representatives, LeMoine Patent Services, PLLC c/o PortfolioIP P.O. Box 52050

Minneapolis, MN 55402 952-473-8800

Date August 21, 2003

By Dana B. Le Maine

Dana LeMoine Reg. No. 40,062

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